

PNP Silicon Epitaxial Planar Transistor

BC856W/BC857W/BC858W

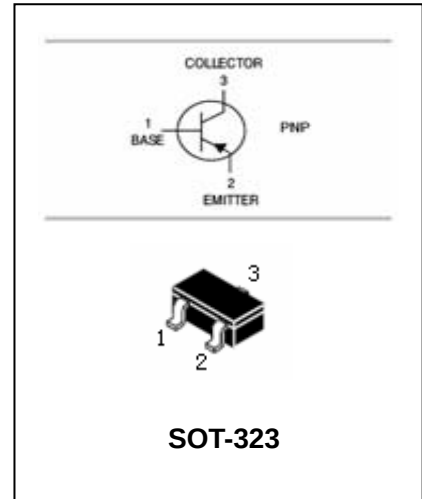
FEATURES

- Ideally suited for automatic insertion.
- Power dissipation.($P_C=200\text{mW}$)



APPLICATIONS

- General purpose switching and amplification application.



ORDERING INFORMATION

Type No.	Marking	Package Code
BC856W	3As/3Bs	SOT-323
BC857W	3E/3F/3G	SOT-323
BC858W	3J/3K/3L	SOT-323

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	BC856W -80	V
		BC857W -50	
		BC858W -30	
V_{CEO}	Collector-Emitter Voltage	BC856W -65	V
		BC857W -45	
		BC858W -30	
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-100	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-65~150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

PNP Silicon Epitaxial Planar Transistor**BC856W/BC857W/BC858W**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$ BC856W BC857W BC858W	-80 -50 -30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$ BC856W BC857W BC858W	-65 -45 -30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	BC856W $V_{CB} = -70V, I_E = 0$ BC857W $V_{CB} = -45V, I_E = 0$ BC858W $V_{CB} = -25V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	BC856W $V_{CE} = -60V, I_B = 0$ BC857W $V_{CE} = -40V, I_B = 0$ BC858W $V_{CE} = -25V, I_B = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -2mA$ BC856AW, BC857AW BC856BW, BC857BW, BC858BW BC857CW, BC858CW	125 220 420	250 475 800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -5mA$		-0.5	mV
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -5mA$		-1.1	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$	100		MHz
Collector capacitance	C_C	$V_{CB} = -10V, f = 1MHz$		4.5	pF

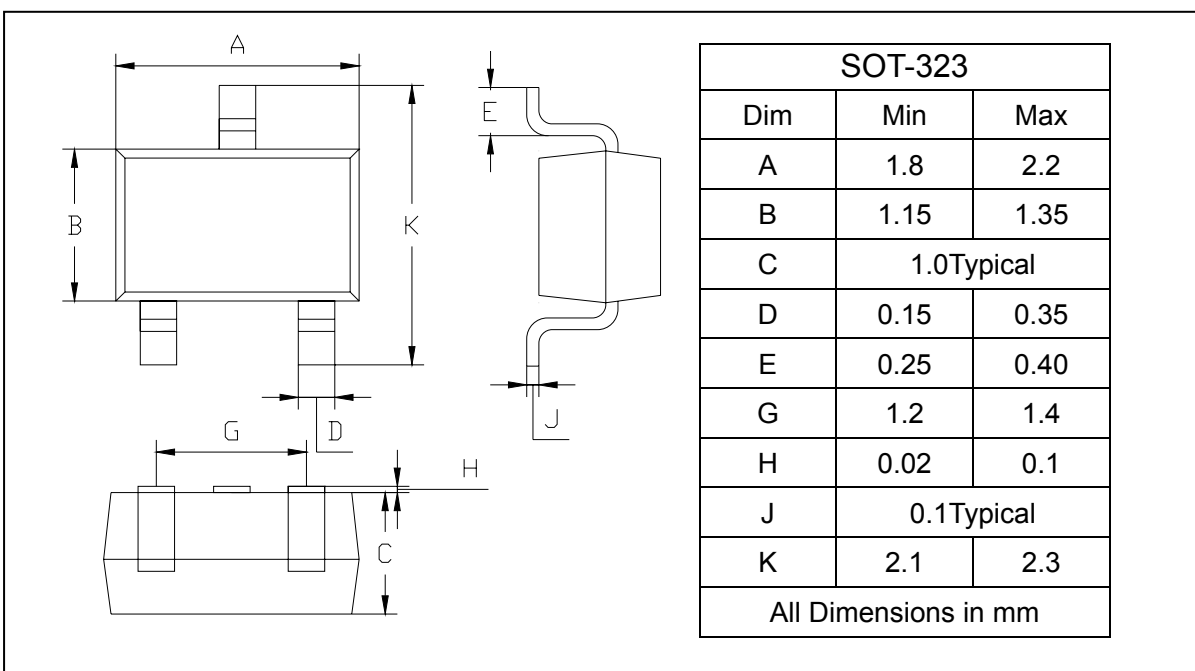
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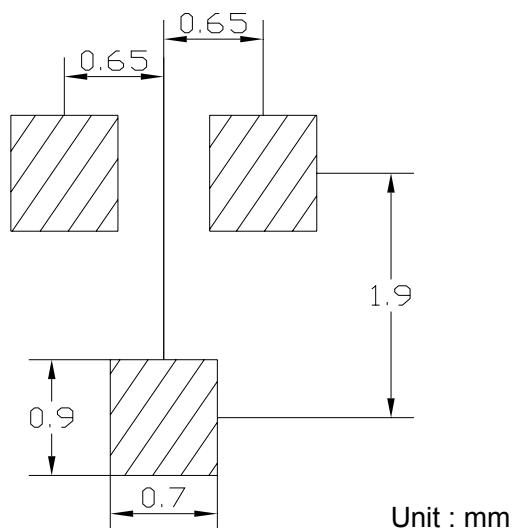
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BC856W/BC857W/BC858W	SOT-323	3000/Tape&Reel